

# Super Barrier Rectifier TM

Using state-of-the-art SBR IC process technology, the following features are made possible in a single device:

Major ratings and characteristics

Characteristics	Values	Units
$I_{F(AV)}$ Rectangular Waveform	40	А
V <sub>RRM</sub>	45	V
V <sub>F</sub> @20A, Tj=125 <sup>0</sup> C	0.40	V, typ
Tj (operating/storage)	-65 to 150	°C

#### ELECTRICAL:

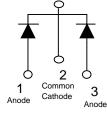
- \* Low Forward Voltage Drop
- \* Reliable High Temperature Operation
- \* Super Barrier Design
- \* Softest, fast switching capability
- \* 150°C Operating Junction Temperature

## Device optimized for low forward voltage drop to maximize efficiency in Power Supply applications

#### MECHANICAL:

\* Molded Plastic TO-3P package





### Maximum Ratings and Electrical Characteristics

	SYMBOL			UNITS
DC Blocking Voltage Working Peak Reverse Voltage Peak Repetitive Reverse Voltage	V <sub>rm</sub> V <sub>rwm</sub> V <sub>rrm</sub>	45		Volts
Average Rectified Forward Current (Rated V <sub>R</sub> -20Khz Square Wave) - 50% duty cycle	Io	40		Amps
Peak Forward Surge Current - 1/2 60hz	I <sub>FSM</sub>	300		Amps
Peak Repetitive Reverse Surge Current (2uS-1Khz)	I <sub>rrm</sub>	3		Amps
Instantaneous Forward Voltage (per leg) I <sub>F</sub> = 20A; T <sub>J</sub> = 25°C I <sub>F</sub> = 20A; T <sub>J</sub> = 125°C	V <sub>F</sub> .	Тур  	Max 0.56 0.46	Volts
Maximum Instantaneous Reverse Current at Rated $V_{RM}$ $T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	I <sub>R</sub>	Тур  	Max 0.5 100	mA mA
Maximum Rate of Voltage Change (at Rated $V_R$ )	dv/dt	10,000		V/uS
Maximum Thermal Resistance JC (per leg)	Rθ <sub>JC</sub>	2		°C/W
Operating and Storage Junction Temperature	TJ	-65 to +150		°C

\* Pulse width < 300 uS, Duty cycle < 2%

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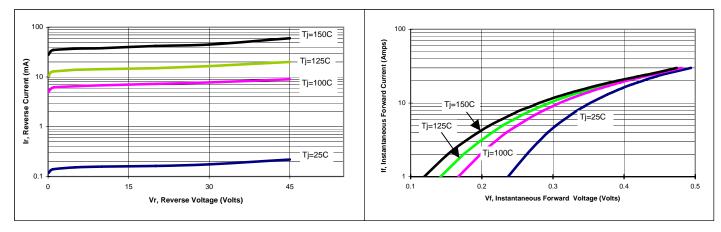


Figure 1: Typical Reverse Current (per leg)

Figure 2: Typical Forward Voltage (per leg)

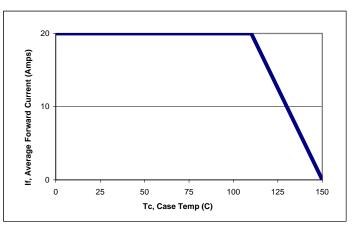


Figure 3: Current Derating, Case (per leg)

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